74HC245; 74HCT245

Octal bus transceiver; 3-state

1. General description

The 74HC245; 74HCT245 is an 8-bit transceiver with 3-state outputs. The device features an output enable ($\overline{OE}$) and send/receive (DIR) for direction control. A HIGH on $\overline{OE}$ causes the outputs to assume a high-impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Complies with JEDEC standard JESD7A
- Input levels:
  - For 74HC245: CMOS level
  - For 74HCT245: TTL level
- Octal bidirectional bus interface
- Non-inverting 3-state outputs
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	**Name**	**Description**	**Version**
74HC245D 74HCT245D	–40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HC245DB 74HCT245DB	–40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74HC245PW 74HCT245PW	–40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HC245BQ 74HCT245BQ	–40 °C to +125 °C	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1

4. Functional diagram

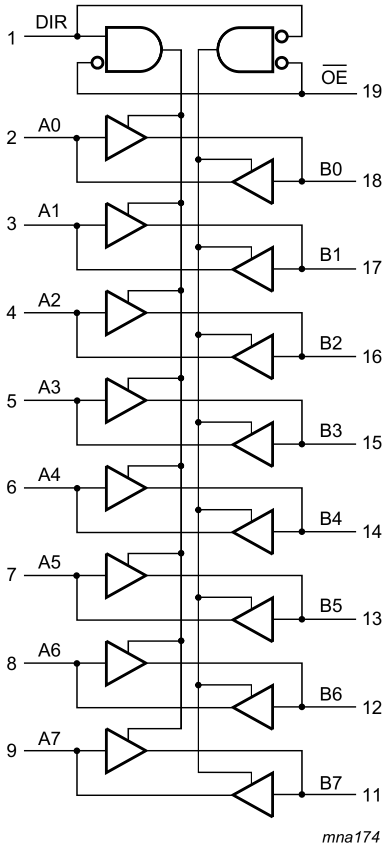


Fig 1. Logic symbol

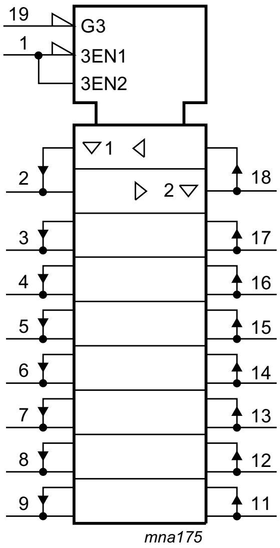


Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning

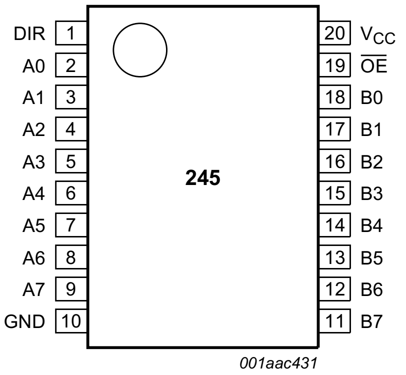
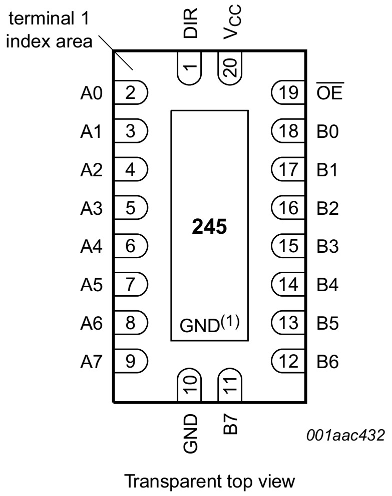


Fig 3. Pin configuration SO20 and (T)SSOP20



(1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 4. Pin configuration DHVQFN20

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DIR	1	direction control
A0, A1, A2, A3, A4, A5, A6, A7	2, 3, 4, 5, 6, 7, 8, 9	data input/output
GND	10	ground (0 V)
B7, B6, B5, B4, B3, B2, B1, B0	11, 12, 13, 14, 15, 16, 17, 18	data input/output
$\overline{OE}$	19	output enable input (active LOW)
V_{CC}	20	supply voltage

6. Functional description

6.1 Function table

Table 3. Function table[1]

Input		Input/output	
$\overline{OE}$	DIR	An	Bn
L	L	A = B	input
L	H	input	B = A
H	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		–0.5	+7	V
I_{IK}	input clamping current	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V	-	±20	mA
I_{OK}	output clamping current	$V_O < –0.5$ V or $V_O > V_{CC} + 0.5$ V	-	±20	mA
I_O	output current	$–0.5$ V $< V_O < V_{CC} + 0.5$ V	-	±35	mA
I_{CC}	supply current		-	70	mA
I_{GND}	ground current		–70	-	mA
T_{stg}	storage temperature		–65	+150	°C
P_{tot}	total power dissipation	SO20, SSOP20, TSSOP20 and DHVQFN20 packages [1]	-	500	mW

[1] For SO20 packages: above 70 °C, P_{tot} derates linearly with 8 mW/K.
For SSOP20 and TSSOP20 packages: above 60 °C, P_{tot} derates linearly with 5.5 mW/K.
For DHVQFN20 packages: above 60 °C, P_{tot} derates linearly with 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	74HC245			74HCT245			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC245										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = –20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = –6.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = –7.8 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 7.8 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	V_I = V_{IH} or V_{IL}; V_{CC} = 6.0 V; V_O = V_{CC} or GND	-	-	±0.5	-	±5.0	-	±10	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
$C_{I/O}$	input/output capacitance		-	10	-	-	-	-	-	pF

Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT245										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = –20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 6.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL}; V_{CC} = 5.5 V; $V_O = V_{CC}$ or GND	-	-	±0.5	-	±5.0	-	±10	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; V_{CC} = 5.5 V; I_O = 0 A	-	-	8.0	-	80	-	160	μA
ΔI_{CC}	additional supply current	$V_I = V_{CC}$ – 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; I_O = 0 A								
		An or Bn inputs	-	40	144	-	180	-	196	μA
		$\overline{OE}$ input	-	150	540	-	675	-	735	μA
		DIR input	-	90	324	-	405	-	441	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
$C_{I/O}$	input/output capacitance		-	10	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; for load circuit see Figure 7.

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		Unit
				Min	Typ	Max	Max (85 °C)	Max (125 °C)	
74HC245									
t_{pd}	propagation delay	An to Bn or Bn to An; see Figure 5	[1]						
		V_{CC} = 2.0 V		-	25	90	115	135	ns
		V_{CC} = 4.5 V		-	9	18	23	27	ns
		V_{CC} = 5.0 V; C_L = 15 pF		-	7	-	-	-	ns
		V_{CC} = 6.0 V		-	7	15	20	23	ns
t_{en}	enable time	$\overline{OE}$ to An or Bn; see Figure 6	[2]						
		V_{CC} = 2.0 V		-	30	150	190	225	ns
		V_{CC} = 4.5 V		-	11	30	38	45	ns
		V_{CC} = 6.0 V		-	9	26	33	38	ns
t_{dis}	disable time	$\overline{OE}$ to An or Bn; see Figure 6	[3]						
		V_{CC} = 2.0 V		-	41	150	190	225	ns
		V_{CC} = 4.5 V		-	15	30	38	45	ns
		V_{CC} = 6.0 V		-	12	26	33	38	ns
t_t	transition time	see Figure 5	[4]						
		V_{CC} = 2.0 V		-	14	60	75	90	ns
		V_{CC} = 4.5 V		-	5	12	15	18	ns
		V_{CC} = 6.0 V		-	4	10	13	15	ns
C_{PD}	power dissipation capacitance	per buffer; V_I = GND to V_{CC}	[5]	-	30	-	-	-	pF

Table 7. Dynamic characteristics *...continued*

GND = 0 V; for load circuit see Figure 7.

Symbol	Parameter	Conditions	25 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Max (85 °C)	Max (125 °C)	
74HCT245								
t_{pd}	propagation delay	An to Bn or Bn to An; see Figure 5 [1]						
		V_{CC} = 4.5 V	-	12	22	28	33	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	10	-	-	-	ns
t_{en}	enable time	$\overline{OE}$ to An or Bn; see Figure 6 [2]	-	16	30	38	45	ns
t_{dis}	disable time	$\overline{OE}$ to An or Bn; see Figure 6 [3]	-	16	30	38	45	ns
t_t	transition time	V_{CC} = 4.5 V; see Figure 5 [4]	-	5	12	15	18	ns
C_{PD}	power dissipation capacitance	per buffer; V_I = GND to V_{CC} – 1.5 V [5]	-	30	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_{en} is the same as t_{PZH} and t_{PZL}.

[3] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

[4] t_t is the same as t_{THL} and t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

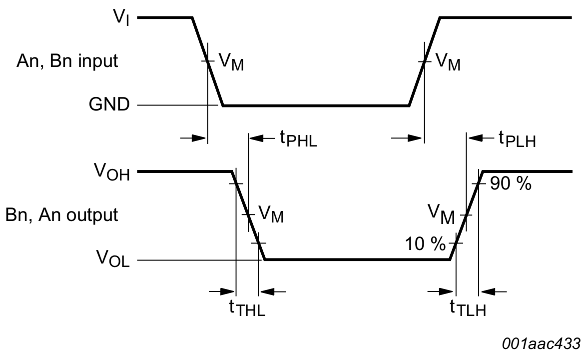
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

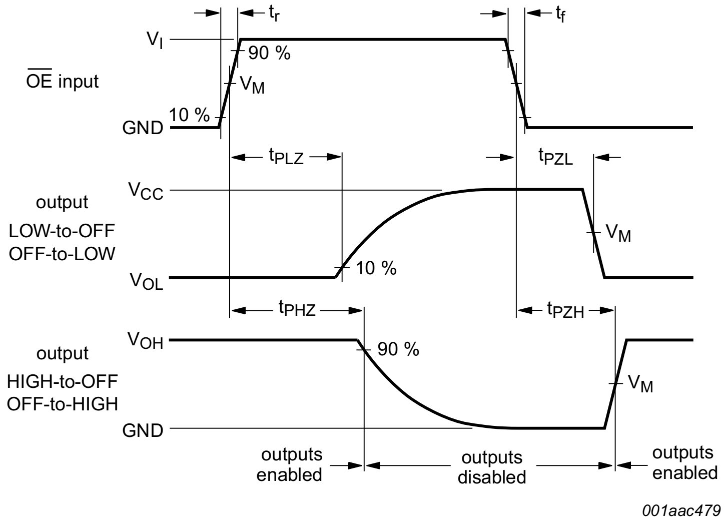
11. Waveforms



Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output drop that occur with the output load.

Fig 5. Input (An, Bn) to output (Bn, An) propagation delays and output transition times



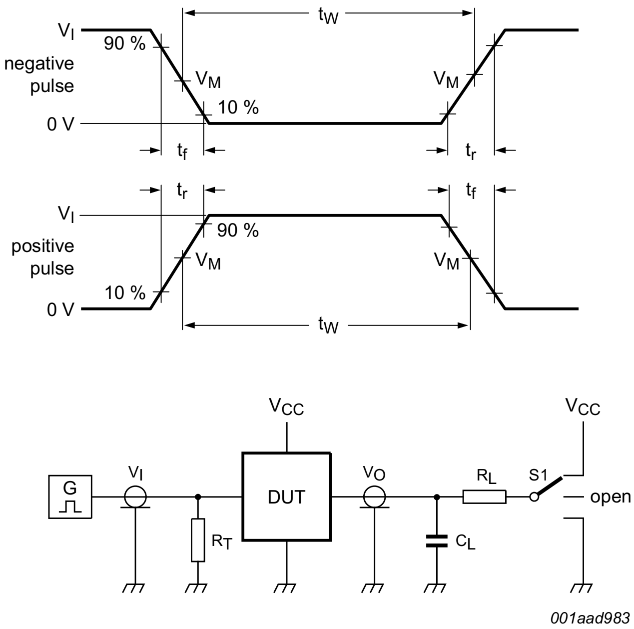
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output drop that occur with the output load.

Fig 6. **3-state output enable and disable times**

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC245	$0.5V_{CC}$	$0.5V_{CC}$
74HCT245	1.3 V	1.3 V



Test data is given in Table 9.

Definitions test circuit:

R$_T$ = Termination resistance should be equal to output impedance Z$_o$ of the pulse generator.

C$_L$ = Load capacitance including jig and probe capacitance.

R$_L$ = Load resistance.

S1 = Test selection switch.

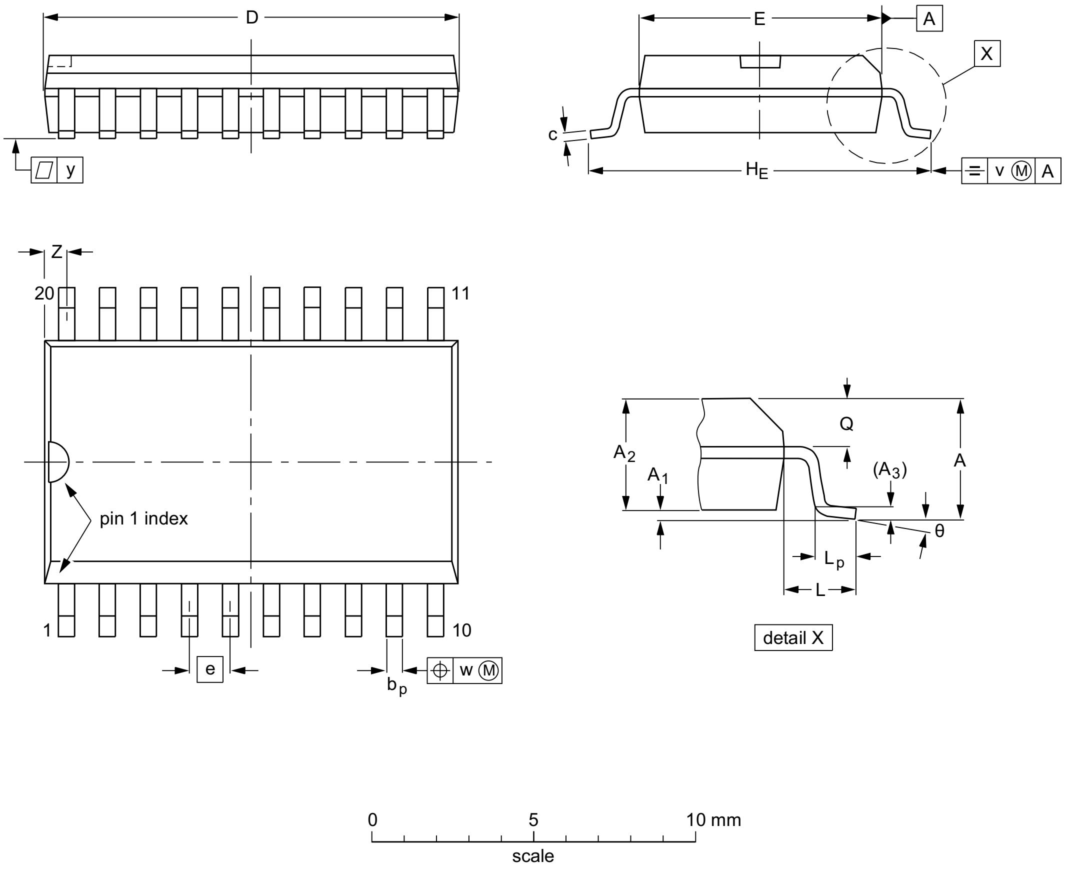
Fig 7. Test circuit for measuring switching times

Table 9. Test data

Type	**Input**		**Load**		**S1 position**		
	V$_I$	**t$_r$, t$_f$**	**C$_L$**	**R$_L$**	**t$_{PHL}$, t$_{PLH}$**	**t$_{PZH}$, t$_{PHZ}$**	**t$_{PZL}$, t$_{PLZ}$**
74HC245	V$_{CC}$	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V$_{CC}$
74HCT245	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V$_{CC}$

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm **SOT163-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D[(1)]	E[(1)]	e	H_E	L	L_p	Q	v	w	y	Z[(1)]	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8° 0°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

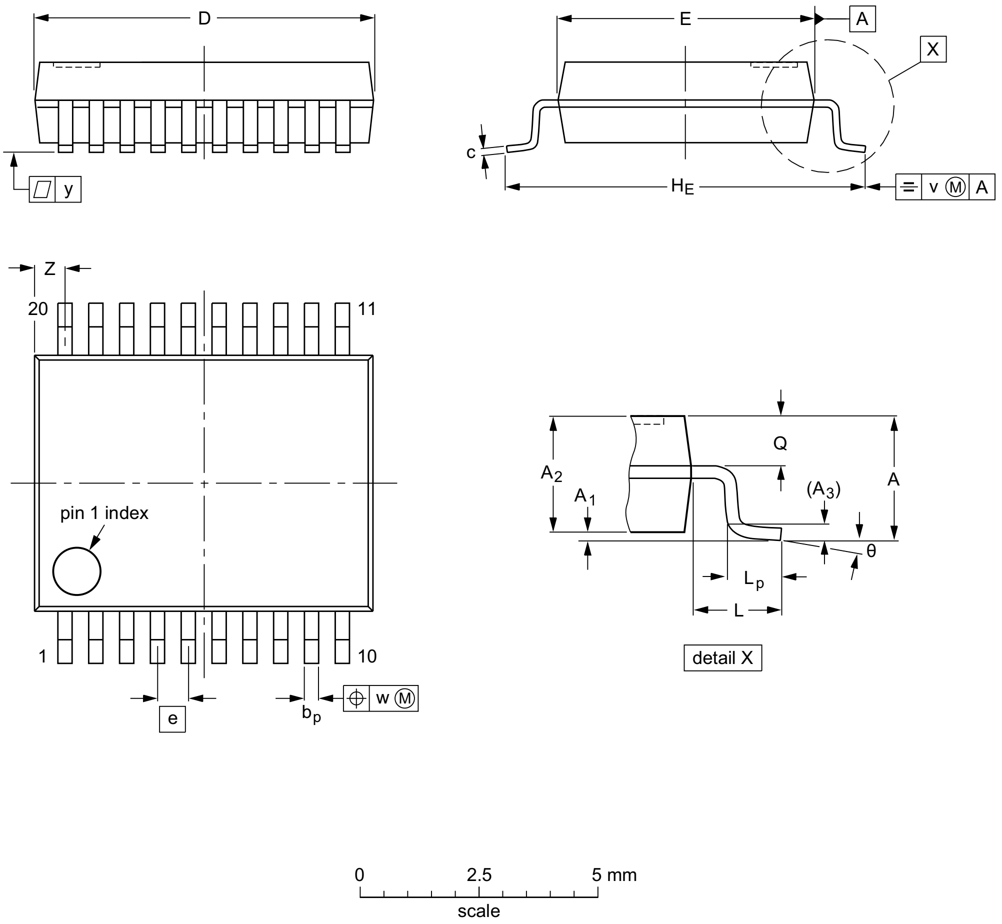
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				~~99-12-27~~ 03-02-19

Fig 8. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm **SOT339-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

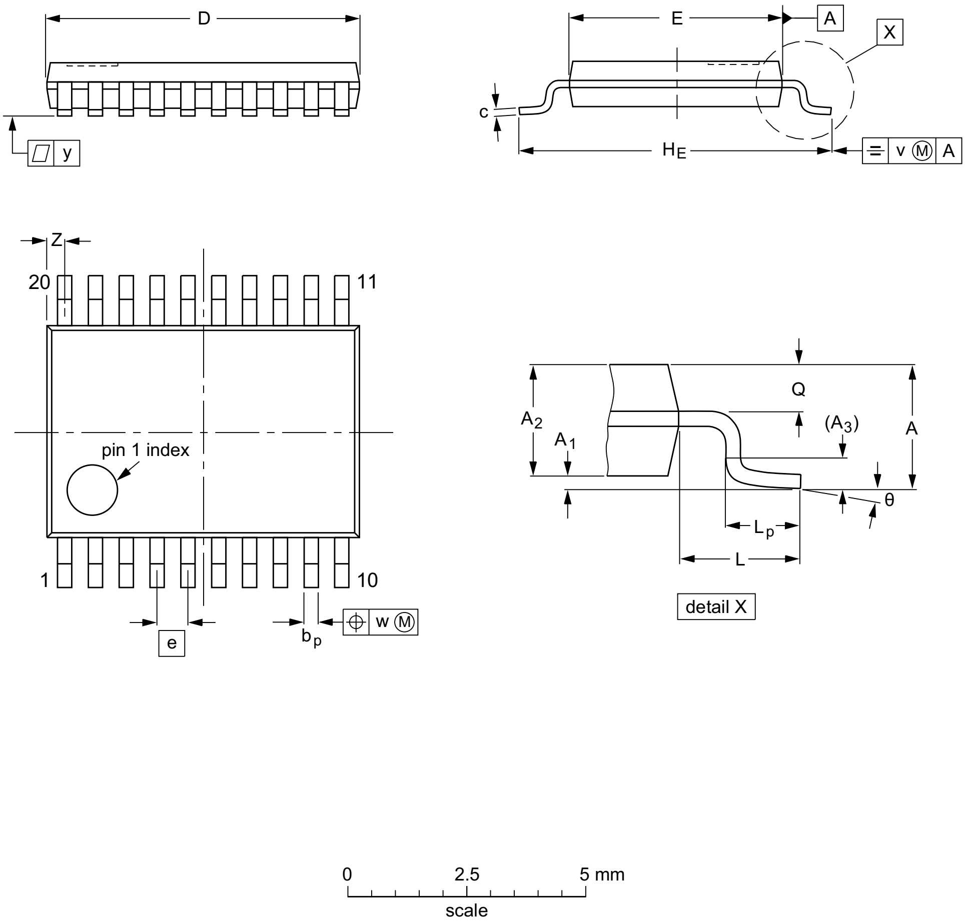
Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT339-1		MO-150				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm **SOT360-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

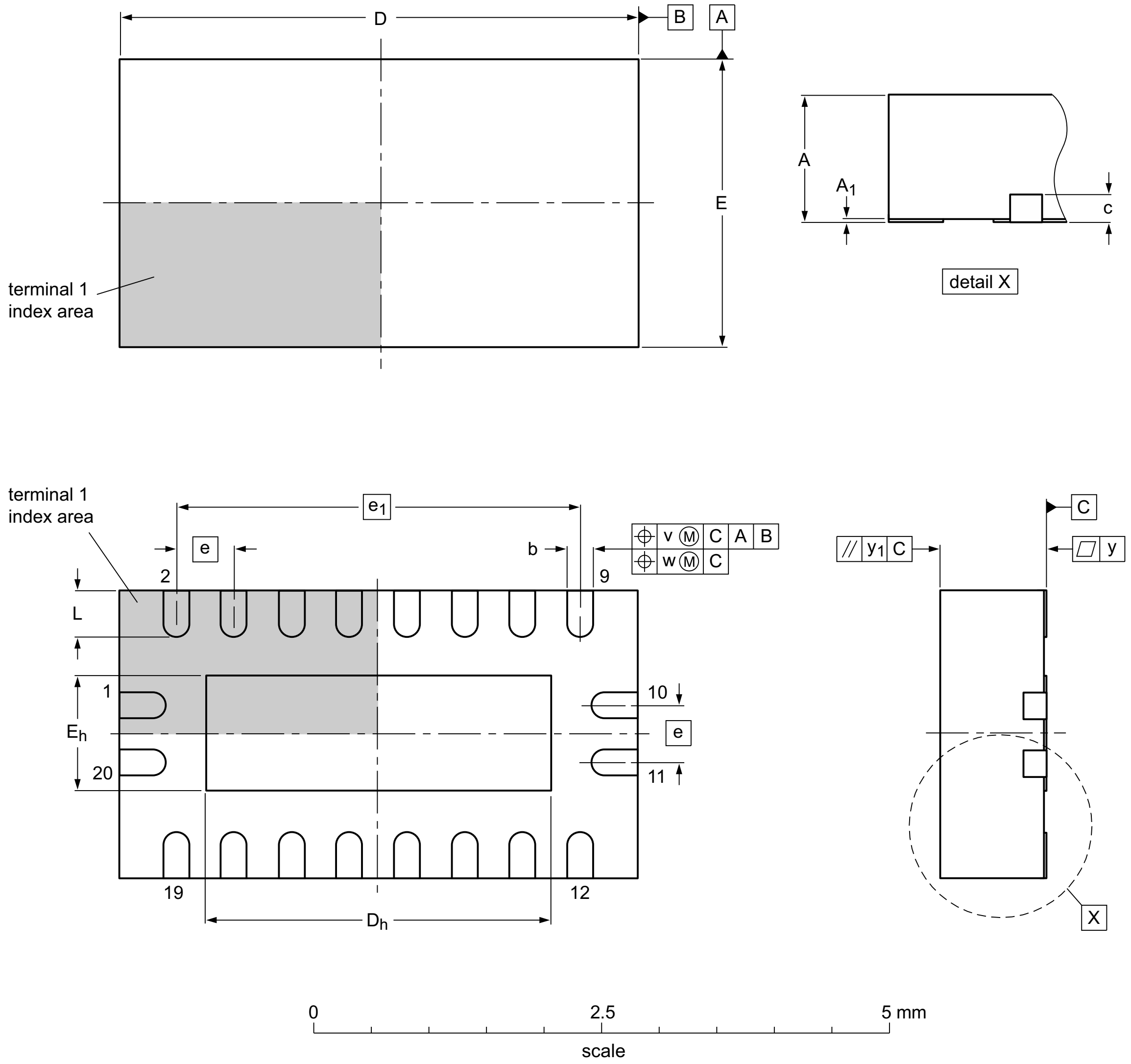
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT360-1		MO-153				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm **SOT764-1**



Dimensions (mm are the original dimensions)

Unit		A(1)	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	max	1.00	0.05	0.30		4.6	3.15	2.6	1.15			0.5				
	nom	0.90	0.02	0.25	0.2	4.5	3.00	2.5	1.00	0.5	3.5	0.4	0.1	0.05	0.05	0.1
	min	0.80	0.00	0.18		4.4	2.85	2.4	0.85			0.3				

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

sot764-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT764-1	- - -	MO-241	- - -			~~03-01-27~~ 14-12-12

Fig 11. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT245 v.4	20160226	Product data sheet	-	74HC_HCT245 v.3
Modifications:	• Type numbers 74HC245N and 74HCT245N (SOT146-1) removed.			
74HC_HCT245 v.3	20050131	Product data sheet	-	74HC_HCT245_CNV v.2
Modifications:	• The format of this data sheet is redesigned to comply with the new presentation and information standard of Philips Semiconductors • Section 3 "Ordering information", Section 5 "Pinning information" and Section 12 "Package outline" are modified to include the DHVQFN20 package.			
74HC_HCT245_CNV v.2	19930930	Product specification	-	-